

Specification of SiD-OUTER-SSSD 6972

Wafer specifications:

n-type silicon, p+ strips, n+ backplane
crystal orientation <100>
320 um thickness +/- 15 um

General ratings

note

Chipsize:	93.531 x 93.531	um	
Number of strips (Readout) :	3679 (1840)	ch	
Strip pitch (Readout) :	25 (50)	um	
Strip P+ width:	8	um	
Strip AL width:	9	um	1st Al Layer
Readout AL width:	4	um	2nd Al Layer

Electrical characters

Coupling Capacitance :	11	pF/cm
Strip AL resistance :	43	Ω /cm
Readout AL resistance :	65	Ω /cm

Inspections & specs

leakage current	5-250V	100V: 3(max) μ A 150V: 4(max) μ A 200V: 5(max) μ A	at Bias ring
Full depletion voltage (Vfd)		100(max) V	at Bias ring
NG channels	Implant open,short AcAL open,short Coupling short Bad Isolation	<20 ch	
Interstrip Capacance		<1.2 pF/cm	2chip/LOT
Poly-Si resistance		10-50 Mohm (Ta=25°C)	at Monitor pattern